

IRF7904PbF

HEXFET® Power MOSFET

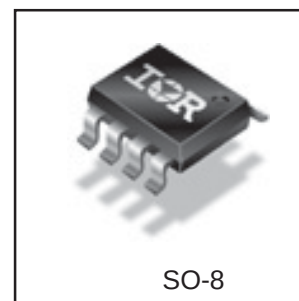
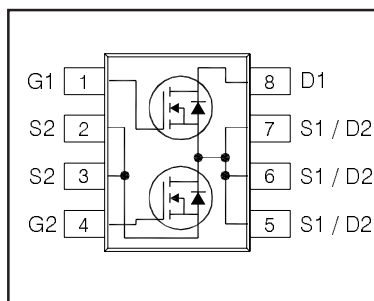
Applications

- Dual SO-8 MOSFET for POL Converters in Notebook Computers, Servers, Graphics Cards, Game Consoles and Set-Top Box

V_{DS}	$R_{DS(on)}$ max	I_D
30V	Q1 16.2m Ω @ $V_{GS} = 10V$	7.6A
	Q2 10.8m Ω @ $V_{GS} = 10V$	11A

Benefits

- Very Low $R_{DS(on)}$ at 4.5V V_{GS}
- Low Gate Charge
- Fully Characterized Avalanche Voltage and Current
- 20V V_{GS} Max. Gate Rating
- Improved Body Diode Reverse Recovery
- 100% Tested for R_G
- Lead-Free



Absolute Maximum Ratings

	Parameter	Q1 Max.	Q2 Max.	Units
V _{DS}	Drain-to-Source Voltage	30		V
V _{GS}	Gate-to-Source Voltage	± 20		
I _D @ T _A = 25°C	Continuous Drain Current, V _{GS} @ 10V	7.6	11	A
I _D @ T _A = 70°C	Continuous Drain Current, V _{GS} @ 10V	6.1	8.9	
I _{DM}	Pulsed Drain Current ①	61	89	
P _D @T _A = 25°C	Power Dissipation	1.4	2.0	W
P _D @T _A = 70°C	Power Dissipation	0.9	1.3	
	Linear Derating Factor	0.011	0.016	W/°C
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to + 150		°C

Thermal Resistance

	Parameter	Q1 Max.	Q2 Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead ⑤	20	20	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient ④ ⑤	90	62.5	

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter		Min.	Typ.	Max.	Units	Conditions	
BV _{DSS}	Drain-to-Source Breakdown Voltage	Q1&Q2	30	—	—	V	V _{GS} = 0V, I _D = 250μA	
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	Q1	—	0.024	—	V/°C	Reference to 25°C, I _D = 1mA	
		Q2	—	0.024	—			
R _{DS(on)}	Static Drain-to-Source On-Resistance	Q1	—	11.4	16.2	mΩ	V _{GS} = 10V, I _D = 7.6A ③	
			—	14.5	20.5		V _{GS} = 4.5V, I _D = 6.1A ③	
		Q2	—	8.6	10.8		V _{GS} = 10V, I _D = 11A ③	
			—	10	13		V _{GS} = 4.5V, I _D = 8.8A ③	
V _{GS(th)}	Gate Threshold Voltage	Q1&Q2	1.35	—	2.25	V	Q1: V _{DS} = V _{GS} , I _D = 25μA	
ΔV _{GS(th)} /ΔT _J	Gate Threshold Voltage Coefficient	Q1	—	-5.0	—	mV/°C	Q2: V _{DS} = V _{GS} , I _D = 50μA	
		Q2	—	-5.0	—			
I _{DSS}	Drain-to-Source Leakage Current	Q1&Q2	—	—	1.0	μA	V _{DS} = 24V, V _{GS} = 0V	
		Q1&Q2	—	—	150		V _{DS} = 24V, V _{GS} = 0V, T _J = 125°C	
I _{GSS}	Gate-to-Source Forward Leakage	Q1&Q2	—	—	100	nA	V _{GS} = 20V	
	Gate-to-Source Reverse Leakage	Q1&Q2	—	—	-100		V _{GS} = -20V	
g _{fs}	Forward Transconductance	Q1	17	—	—	S	V _{DS} = 15V, I _D = 6.1A	
		Q2	23	—	—		V _{DS} = 15V, I _D = 8.8A	
Q _g	Total Gate Charge	Q1	—	7.5	11	nC	Q1 V _{DS} = 15V V _{GS} = 4.5V, I _D = 6.1A	
		Q2	—	14	21			
Q _{gs1}	Pre-V _{th} Gate-to-Source Charge	Q1	—	2.2	—			
		Q2	—	3.7	—			
Q _{gs2}	Post-V _{th} Gate-to-Source Charge	Q1	—	0.6	—		Q2 V _{DS} = 15V V _{GS} = 4.5V, I _D = 8.8A	
		Q2	—	1.1	—			
Q _{gd}	Gate-to-Drain Charge	Q1	—	2.5	—			
		Q2	—	4.8	—			
Q _{godr}	Gate Charge Overdrive	Q1	—	2.2	—			
		Q2	—	4.4	—			
Q _{sw}	Switch Charge (Q _{gs2} + Q _{gd})	Q1	—	3.1	—			
		Q2	—	5.9	—			
Q _{oss}	Output Charge	Q1	—	4.5	—	nC	V _{DS} = 16V, V _{GS} = 0V	
		Q2	—	9.1	—			
R _G	Gate Resistance	Q1	—	3.2	4.8	Ω	Q1 V _{DD} = 15V, V _{GS} = 4.5V I _D = 6.1A	
		Q2	—	2.9	4.4			
t _{d(on)}	Turn-On Delay Time	Q1	—	6.9	—	ns		Q2 V _{DD} = 15V, V _{GS} = 4.5V I _D = 8.8A Clamped Inductive Load
		Q2	—	7.8	—			
t _r	Rise Time	Q1	—	7.3	—			
		Q2	—	10	—			
t _{d(off)}	Turn-Off Delay Time	Q1	—	10	—			
		Q2	—	15	—			
t _f	Fall Time	Q1	—	3.2	—			
		Q2	—	4.6	—			
C _{iss}	Input Capacitance	Q1	—	910	—	pF	V _{GS} = 0V V _{DS} = 15V f = 1.0MHz	
		Q2	—	1780	—			
C _{oss}	Output Capacitance	Q1	—	190	—			
		Q2	—	390	—			
C _{rss}	Reverse Transfer Capacitance	Q1	—	94	—			
		Q2	—	180	—			

Avalanche Characteristics

	Parameter	Typ.	Q1 Max.	Q2 Max.	Units
E_{AS}	Single Pulse Avalanche Energy ①	—	140	250	mJ
I_{AR}	Avalanche Current ①	—	6.1	8.8	A

Diode Characteristics

	Parameter		Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	Q1	—	—	1.8	A	MOSFET symbol showing the integral reverse p-n junction diode.
		Q2	—	—	2.5		
I_{SM}	Pulsed Source Current (Body Diode) ①	Q1	—	—	61	A	
		Q2	—	—	88		
V_{SD}	Diode Forward Voltage	Q1	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 6.1A, V_{GS} = 0V$ ③
		Q2	—	—	1.0		$T_J = 25^\circ\text{C}, I_S = 8.8A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	Q1	—	11	17	ns	Q1 $T_J = 25^\circ\text{C}, I_F = 6.1A, V_{DD} = 15V, di/dt = 100A/\mu s$ ③
		Q2	—	16	24		
Q_{rr}	Reverse Recovery Charge	Q1	—	2.6	3.9	nC	Q2 $T_J = 25^\circ\text{C}, I_F = 8.8A, V_{DD} = 15V, di/dt = 100A/\mu s$ ③
		Q2	—	6.9	10		

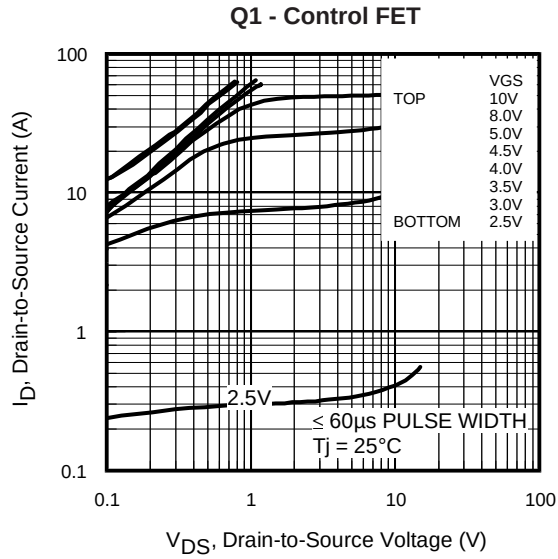


Fig 1. Typical Output Characteristics

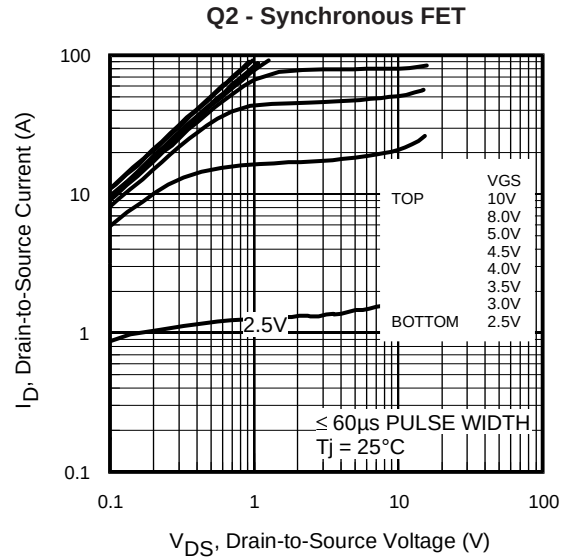


Fig 2. Typical Output Characteristics

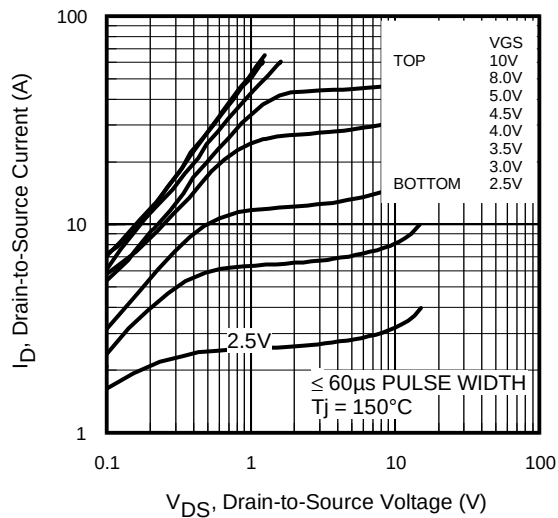


Fig 3. Typical Output Characteristics

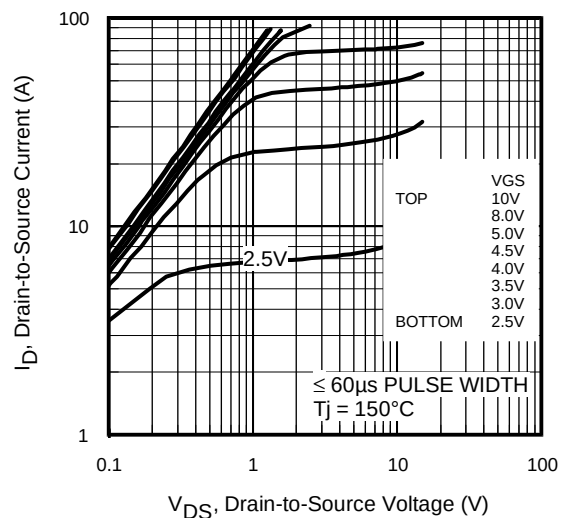


Fig 4. Typical Output Characteristics

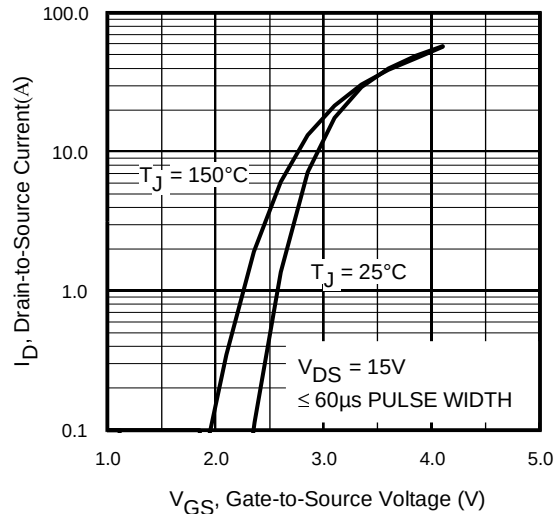


Fig 5. Typical Transfer Characteristics

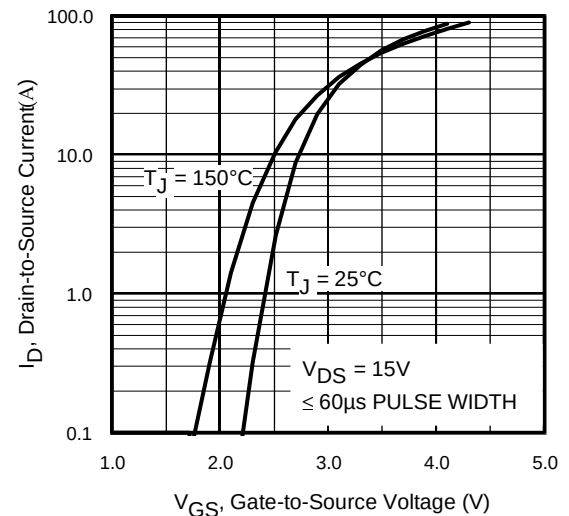


Fig 6. Typical Transfer Characteristics

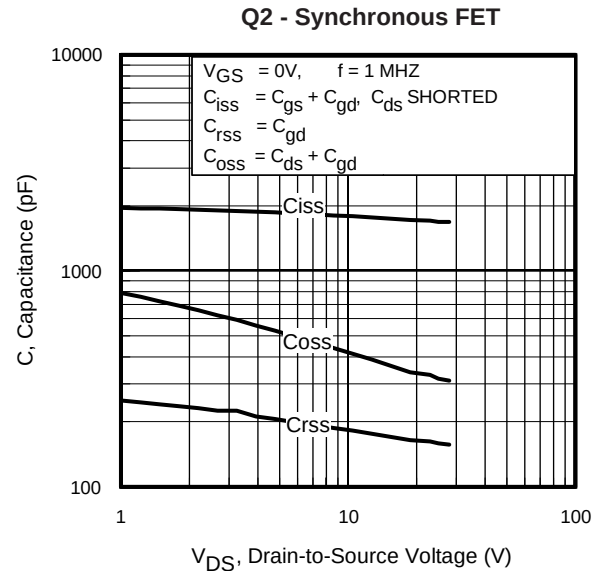
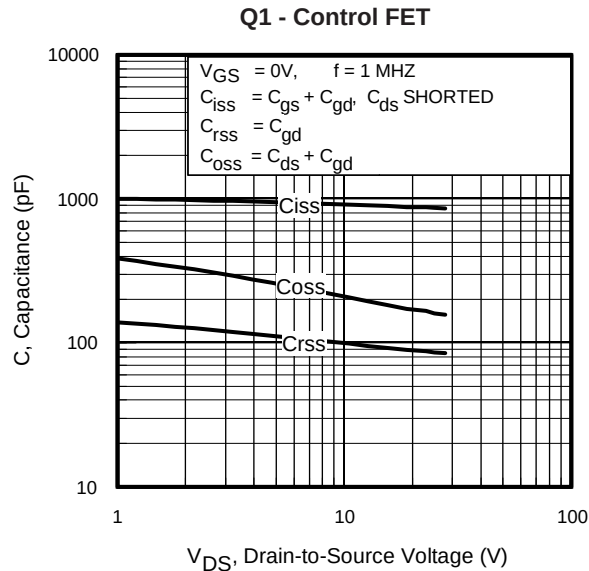


Fig 7. Typical Capacitance vs. Drain-to-Source Voltage **Fig 8.** Typical Capacitance vs. Drain-to-Source Voltage

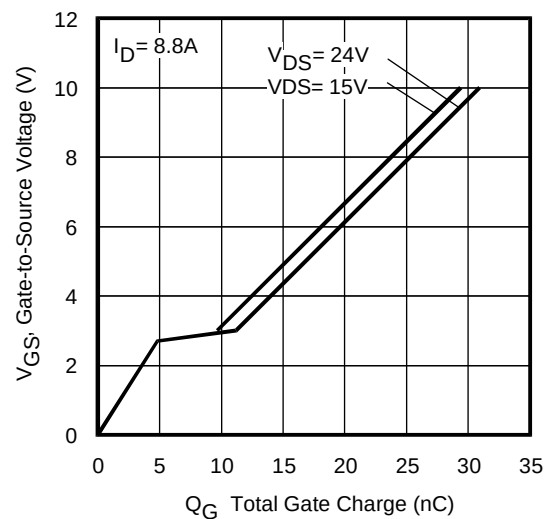
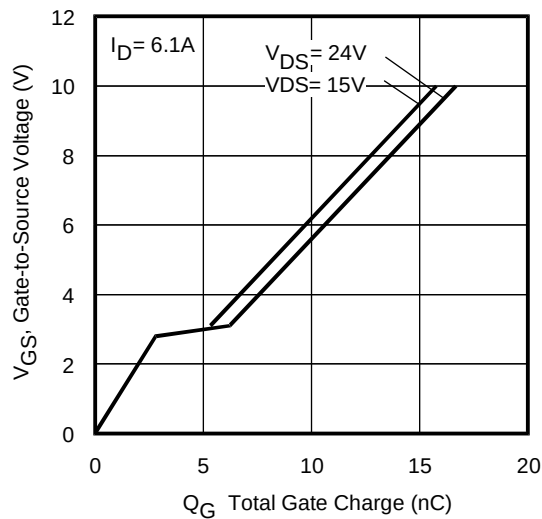
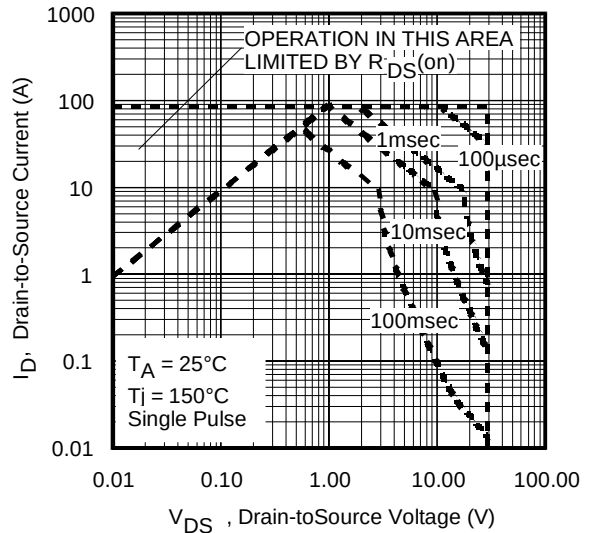
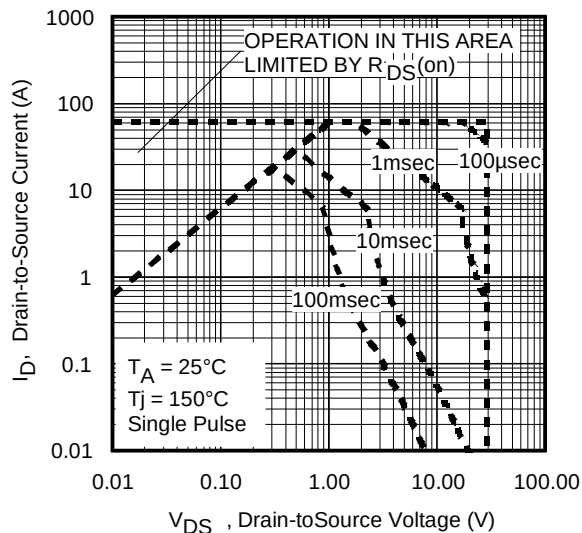


Fig 9. Typical Gate Charge vs. Gate-to-Source Voltage

Fig 10. Typical Gate Charge vs. Gate-to-Source Voltage



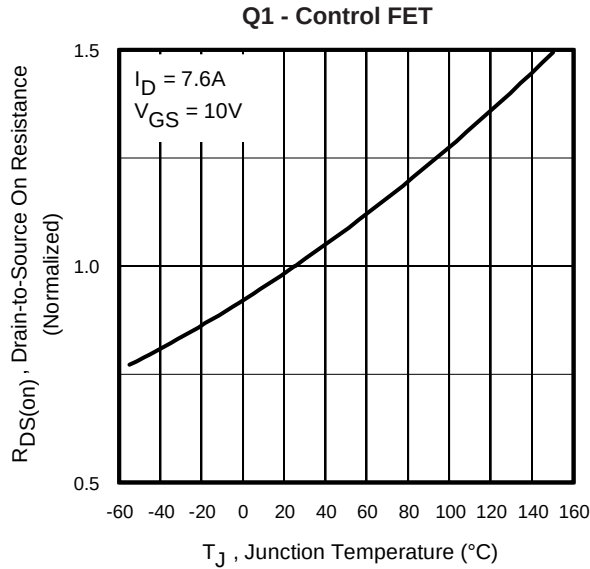


Fig 13. Normalized On-Resistance vs. Temperature

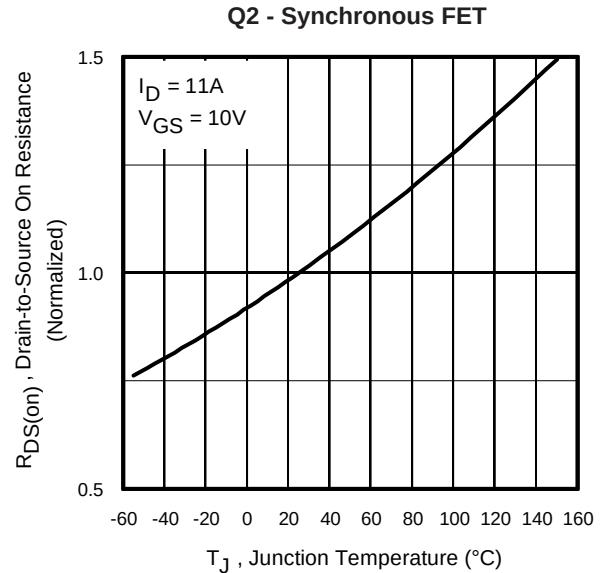


Fig 14. Normalized On-Resistance vs. Temperature

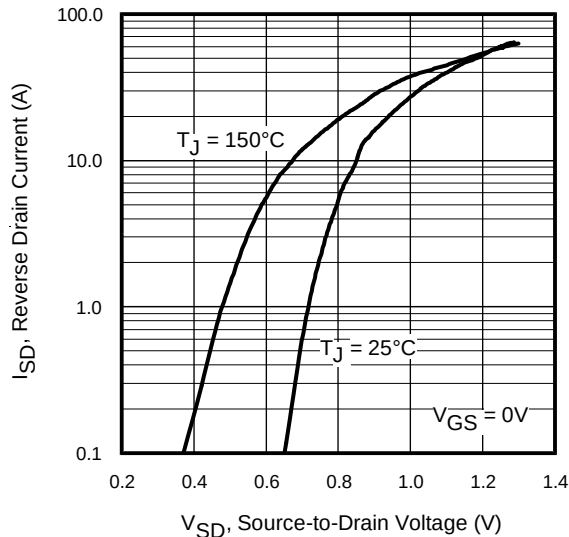


Fig 15. Typical Source-Drain Diode Forward Voltage

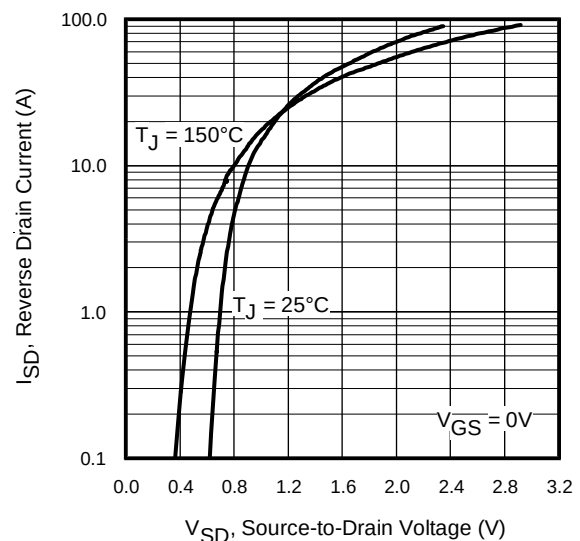


Fig 16. Typical Source-Drain Diode Forward Voltage

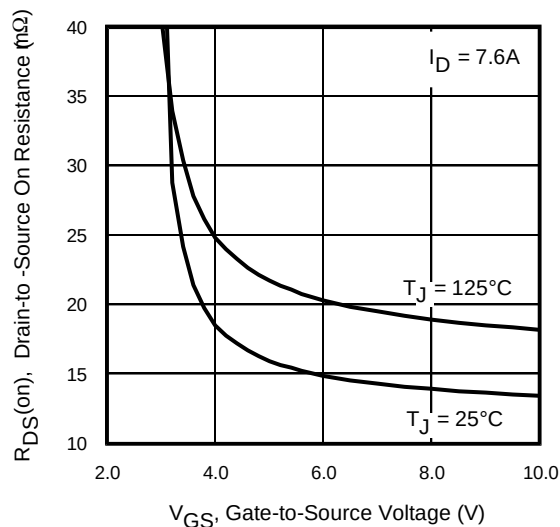


Fig 17. Typical On-Resistance vs. Gate Voltage

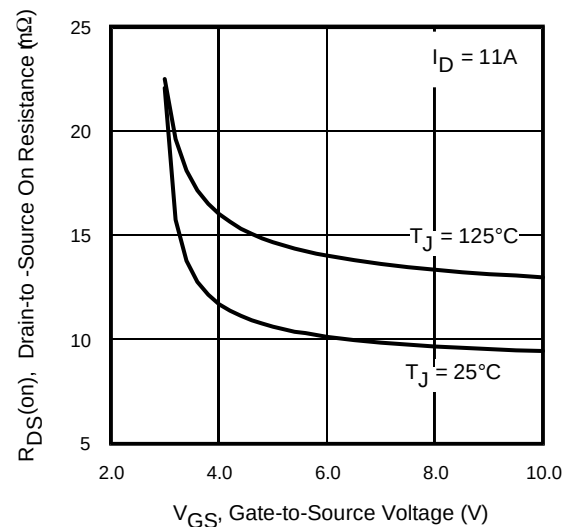


Fig 18. Typical On-Resistance vs. Gate Voltage

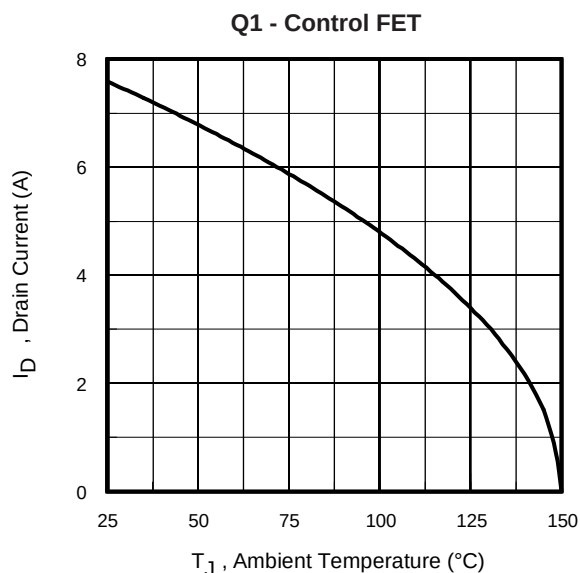


Fig 19. Maximum Drain Current vs. Ambient Temp.

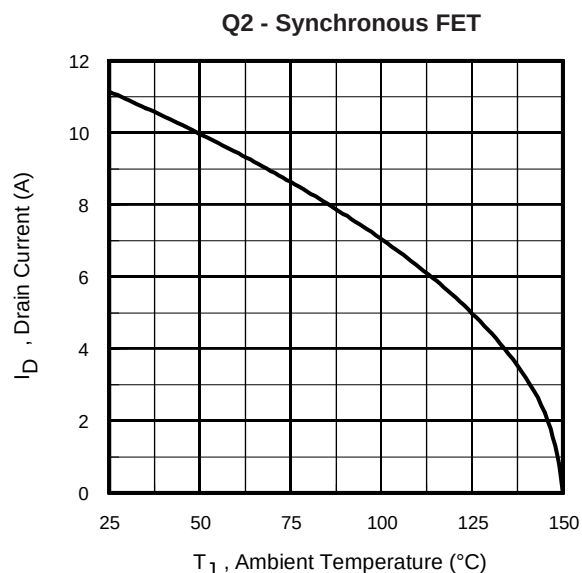


Fig 20. Maximum Drain Current vs. Ambient Temp.

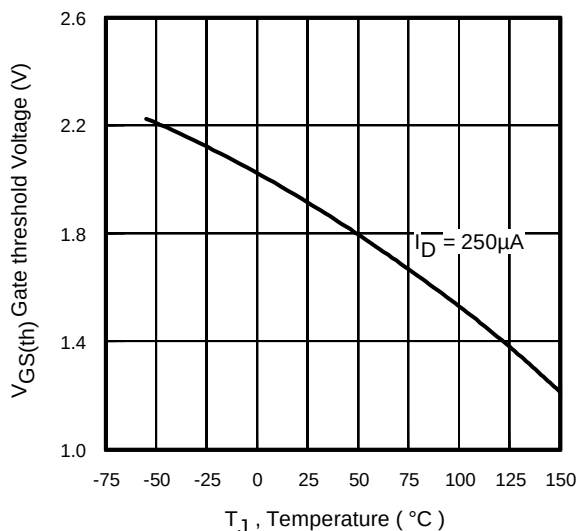


Fig 21. Threshold Voltage vs. Temperature

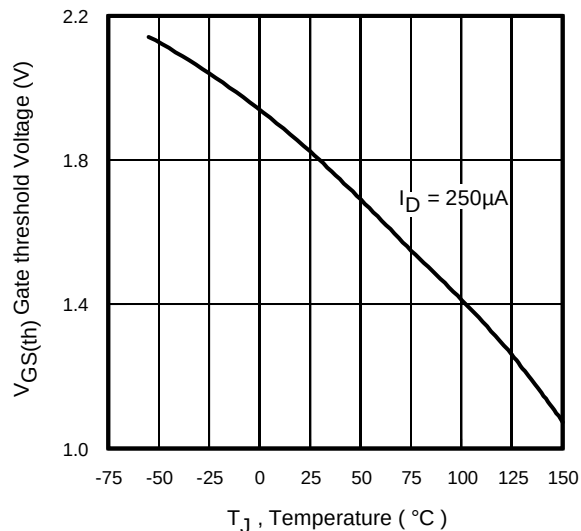


Fig 22. Threshold Voltage vs. Temperature

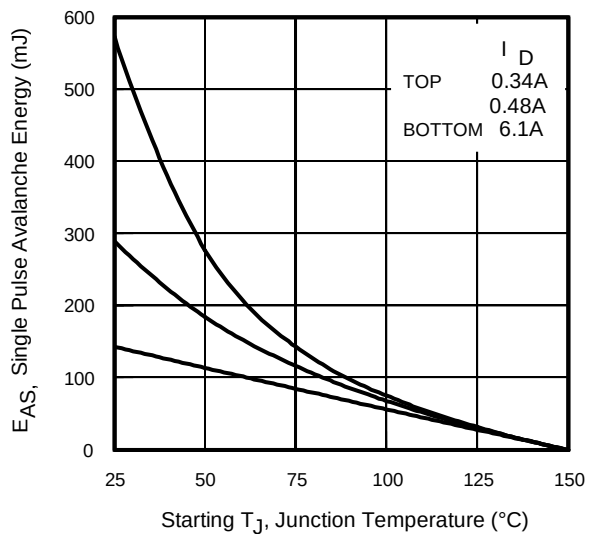


Fig 23. Maximum Avalanche Energy vs. Drain Current

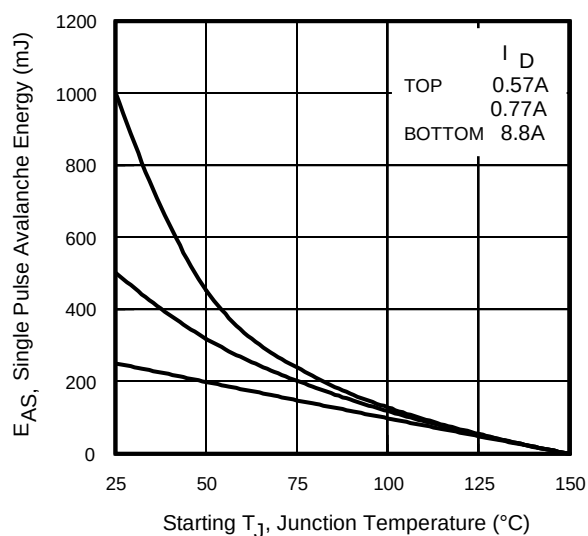


Fig 24. Maximum Avalanche Energy vs. Drain Current

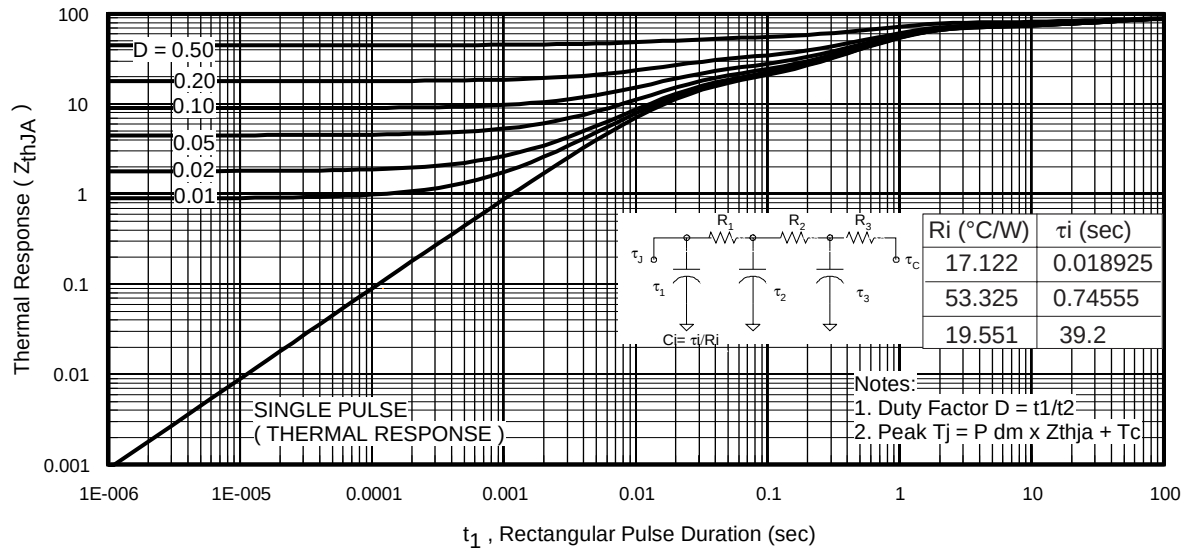


Fig 25. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient (Q1)

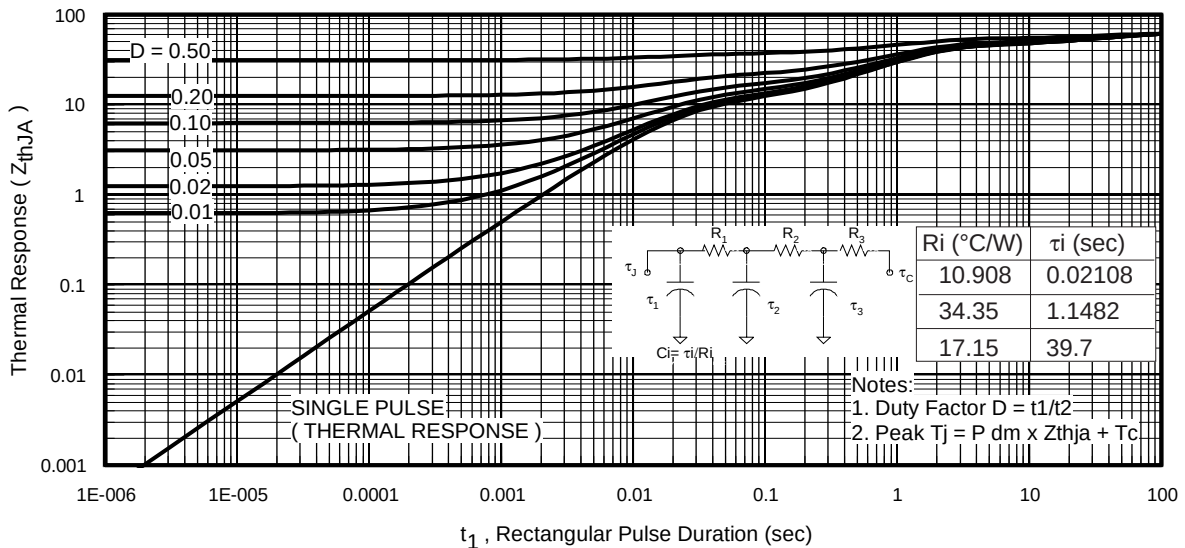


Fig 26. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient (Q2)

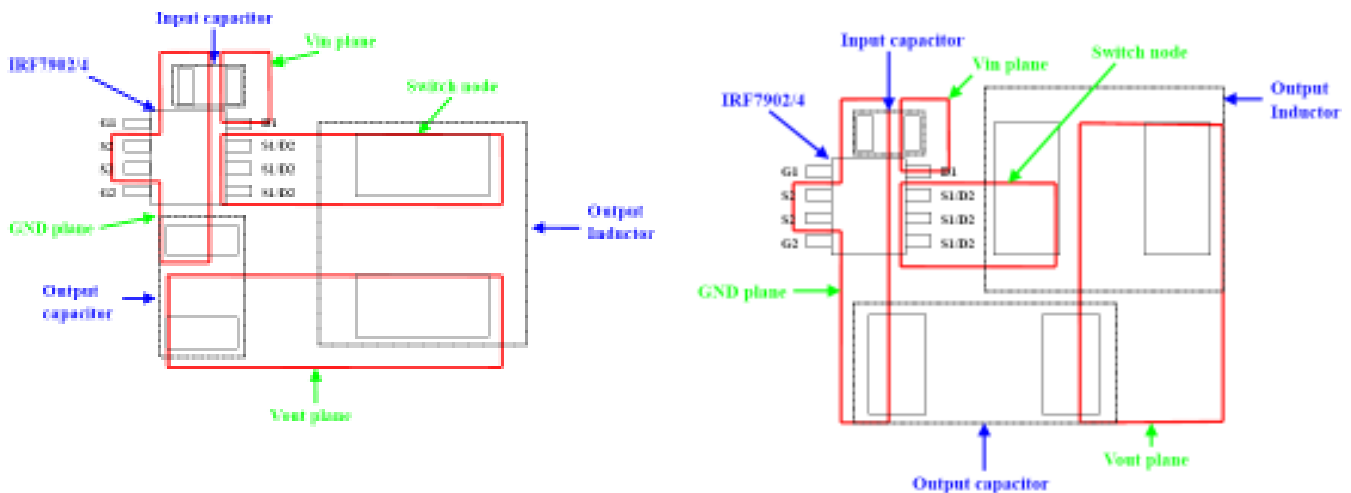


Fig 27. Layout Diagram

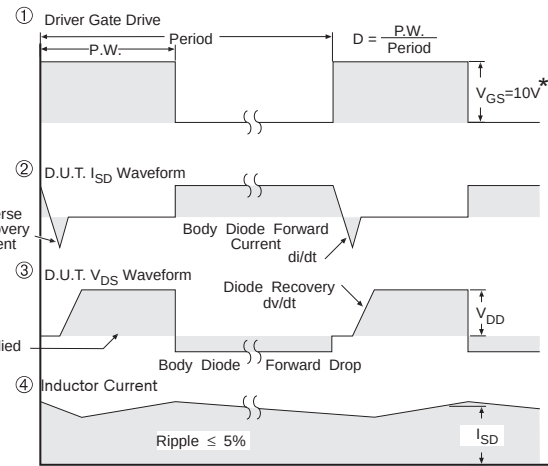
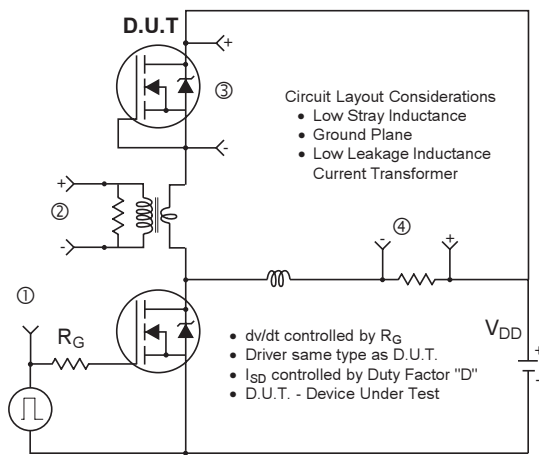


Fig 28. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

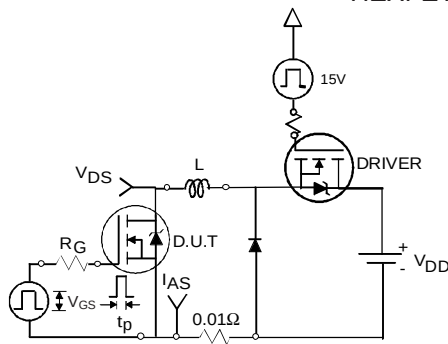


Fig 29a. Unclamped Inductive Test Circuit

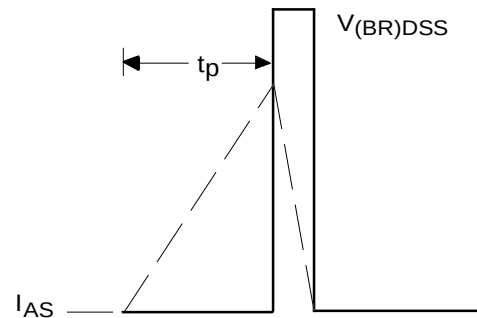


Fig 29b. Unclamped Inductive Waveforms

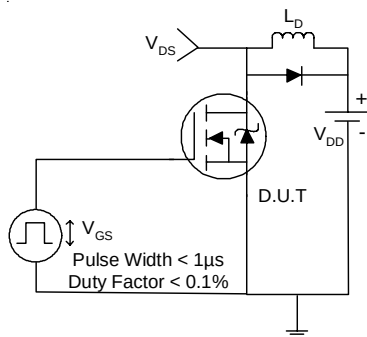


Fig 30a. Switching Time Test Circuit

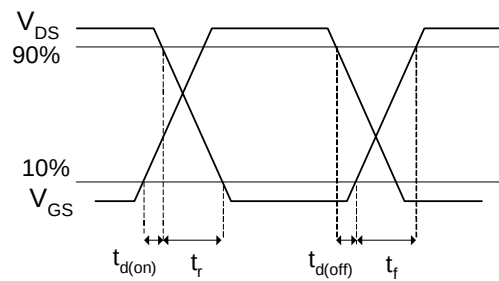


Fig 30b. Switching Time Waveforms

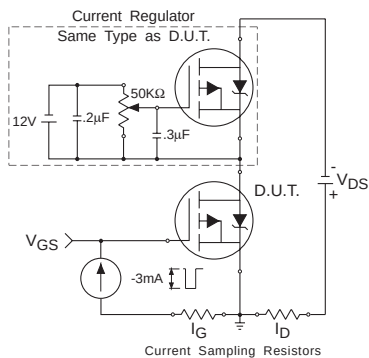


Fig 31a. Gate Charge Test Circuit

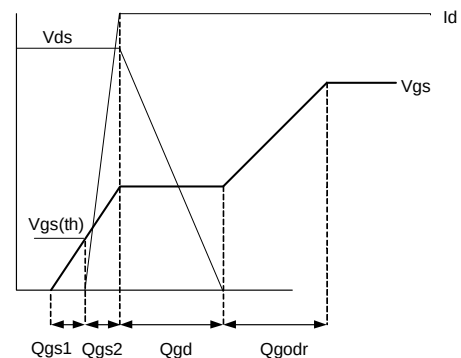
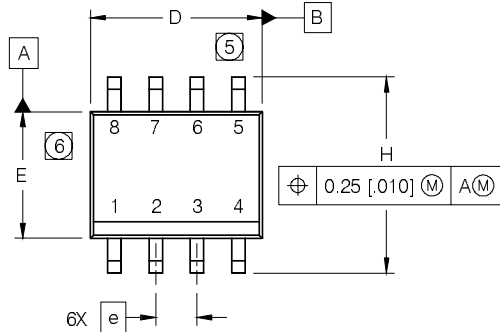


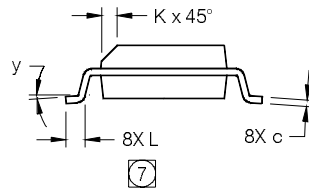
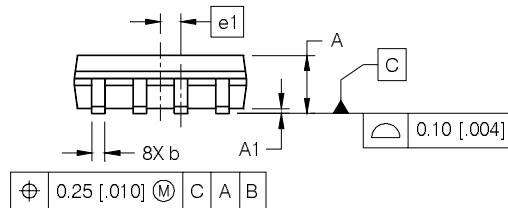
Fig 31b. Gate Charge Waveform

SO-8 Package Outline

Dimensions are shown in millimeters (inches)



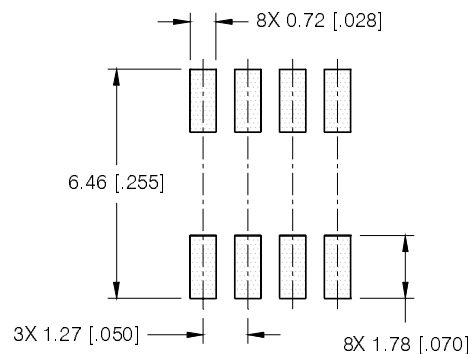
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



NOTES:

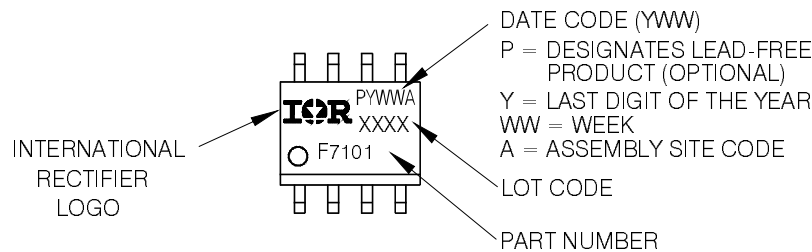
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



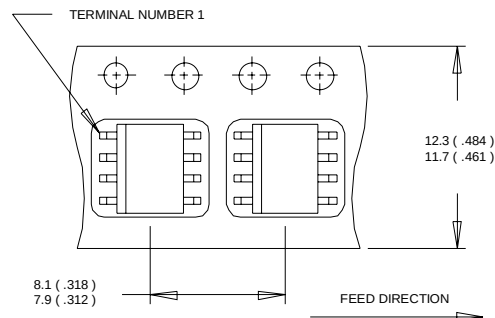
SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

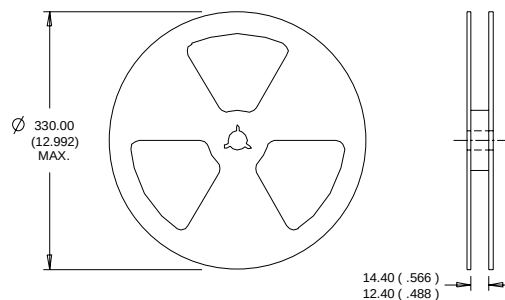


SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, Q1: $L = 7.7\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 6.1\text{A}$; Q2: $L = 6.5\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 8.8\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board.
- ⑤ R_θ is measured at T_J approximately 90°C .

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualification Standards can be found on IR's Web site.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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